Ordering number : ENN7532

P-Channel Silicon MOSFET

SCH1302



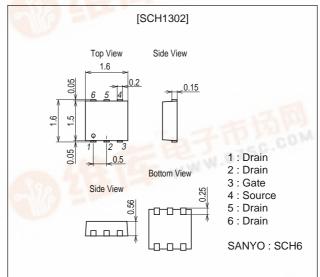
Ultrahigh-Speed Switching Applications

Features

- · Low ON-resistance.
- · Ultrahigh-speed switching.
- · 1.8V drive.

Package Dimensions

unit : mm 2221



Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	VDSS		-20	V
Gate-to-Source Voltage	VGSS		±10	V
Drain Current (DC)	ID		-2	Α
Drain Current (Pulse)	IDP	PW≤10μs, duty cycle≤1%	-8	Α
Allowable Power Dissipation	PD	Mounted on a ceramic board (900mm ² X0.8mm)	0.8	W
Channel Temperature	Tch	- 51 (0 =	150	°C
Storage Temperature	Tstg		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions		Ratings		
			min	typ	max	Unit
Drain-to-Source Breakdown Voltage	V(BR)DSS	I _D =-1mA, V _G S=0	-20			V
Zero-Gate Voltage Drain Current	I _{DSS} 1	V _{DS} =-20V, V _{GS} =0			-10	μΑ
	I _{DSS} 2	V _{DS} =-4V, V _{GS} =0		-	-1	μΑ
Gate-to-Source Leakage Current	IGSS1	V _{GS} =±8V, V _{DS} =0		W (a)	±10	μΑ
	IGSS2	V _{GS} =±4V, V _{DS} =0	THE .	MAL AL	±1	μΑ
Cutoff Voltage	VGS(off)	V _{DS} =-10V, I _D =-1mA	-0.3		-1.0	V
Forward Transfer Admittance	yfs	Vps=-10V, lp=-1A	1.8	3.0		S

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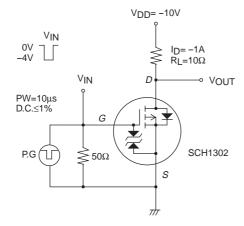
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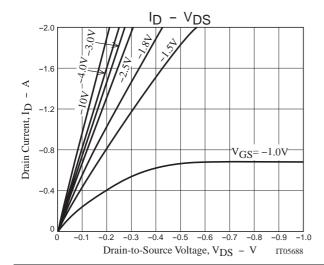
SCH1302

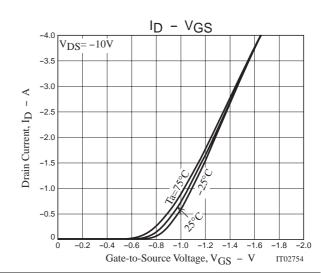
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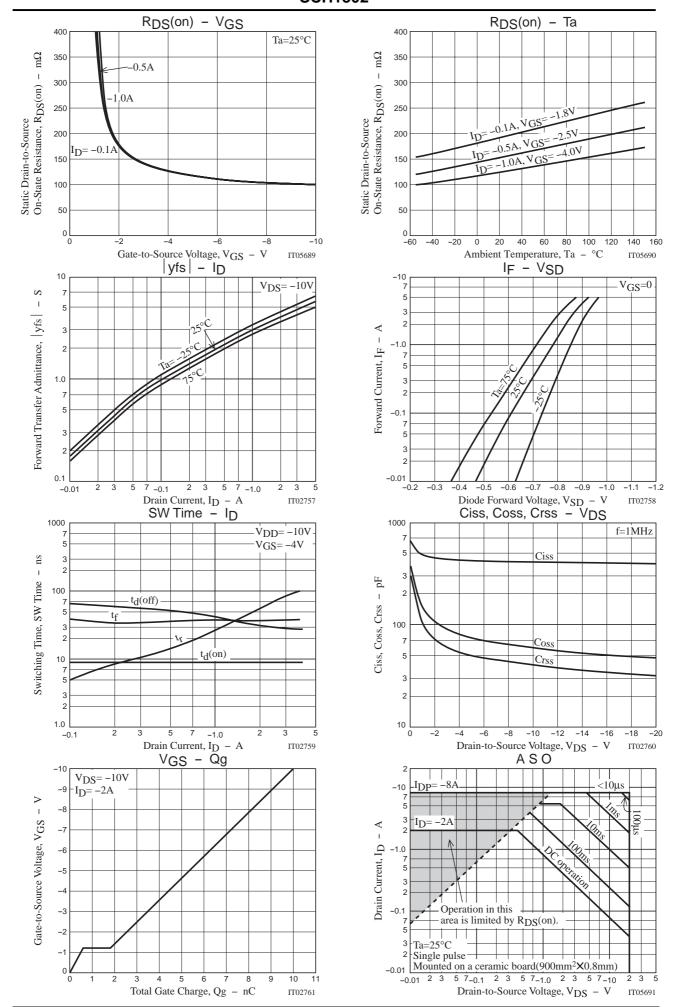
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Unit
Static Drain-to-Source On-State Resistance	RDS(on)1	ID=-1A, VGS=-4V		125	165	mΩ
	R _{DS} (on)2	I _D =-0.5A, V _G S=-2.5V		155	220	mΩ
	R _{DS} (on)3	I _D =-0.1A, V _G S=-1.8V		195	280	mΩ
Input Capacitance	Ciss	V _{DS} =-10V, f=1MHz		410		pF
Output Capacitance	Coss	V _{DS} =-10V, f=1MHz		60		pF
Reverse Transfer Capacitance	Crss	V _{DS} =-10V, f=1MHz		40		pF
Turn-ON Delay Time	td(on)	See specified Test Circuit.		9		ns
Rise Time	t _r	See specified Test Circuit.		27		ns
Turn-OFF Delay Time	t _d (off)	See specified Test Circuit.		42		ns
Fall Time	tf	See specified Test Circuit.		38		ns
Total Gate Charge	Qg	V _{DS} =-10V, V _{GS} =-10V, I _D =-2A		10		nC
Gate-to-Source Charge	Qgs	V _{DS} =-10V, V _{GS} =-10V, I _D =-2A		0.6		nC
Gate-to-Drain "Miller" Charge	Qgd	V _{DS} =-10V, V _{GS} =-10V, I _D =-2A		1.2		nC
Diode Forward Voltage	VSD	I _S =-2A, V _G S=0		-0.88	-1.2	V

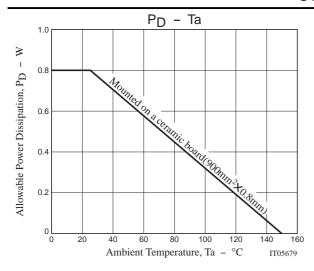
Switching Time Test Circuit











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